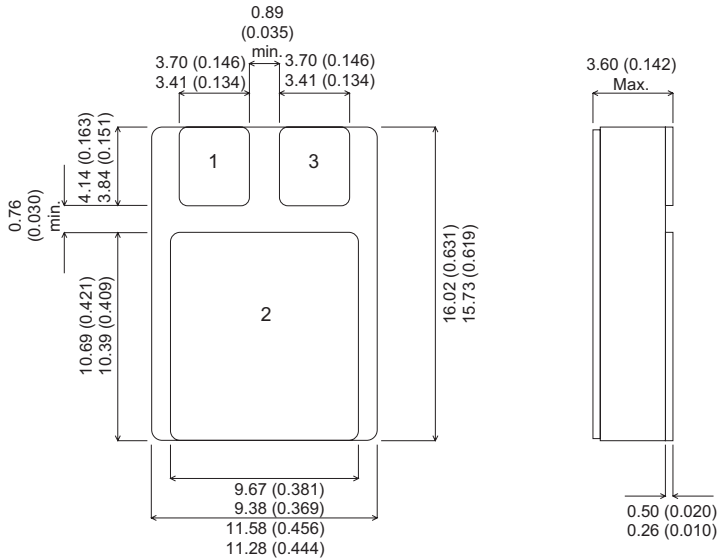


**MECHANICAL DATA**

Dimensions in mm



**SMD1 (TO-276AB) CERAMIC PACKAGE**

**DUAL SCHOTTKY  
 BARRIER DIODE  
 IN CERAMIC SURFACE  
 MOUNT PACKAGE FOR  
 HI-REL APPLICATIONS**

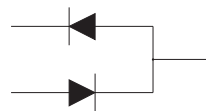
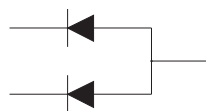
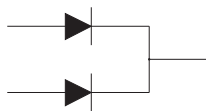
**FEATURES**

- HERMETIC CERAMIC PACKAGE
- AVAILABLE IN COMMON CATHODE, COMMON ANODE AND SERIES VERSIONS
- SCREENING OPTIONS AVAILABLE
- OUTPUT CURRENT 30A
- LOW  $V_F$
- LOW LEAKAGE

**Common Cathode**  
**SB30-45M**

**Common Anode**  
**SB30-45A**

**Series Connection**  
**SB30-45R**



1 = A<sub>1</sub> Anode 1  
 2 = K Cathode  
 3 = A<sub>2</sub> Anode 2

1 = K<sub>1</sub> Cathode 1  
 2 = A Anode  
 3 = K<sub>2</sub> Cathode 2

1 = K<sub>1</sub> Cathode 1  
 2 = Centre Tap  
 3 = A<sub>2</sub> Anode

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^\circ C$  unless otherwise stated)

$V_{RRM}$	Peak Repetitive Reverse Voltage	45V
$V_{RSM}$	Peak Non-Repetitive Reverse Voltage	45V
$V_R$	Continuous Reverse Voltage	45V
$I_{F(AV)}$	Maximum Average Forward Current	30A
$I_{FSM}$	Peak Non-Repetitive Surge Current at 50Hz (per leg)	245A
$T_{STG}$	Storage Temperature Range	-55°C to 150°C
$T_J$	Maximum Operating Junction Temperature	150°C

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

**ELECTRICAL CHARACTERISTICS** ( $T_{CASE} = 25^{\circ}C$  unless otherwise stated)

Parameter		Test Conditions		Min.	Typ.	Max.	Unit
$V_F$	Maximum Forward Voltage Drop (per diode)*	$I_F = 15A$	$T_J = 25^{\circ}C$			0.6	V
		$I_F = 30A$	$T_J = 25^{\circ}C$			0.75	
		$I_F = 15A$	$T_J = 125^{\circ}C$			0.55	
		$I_F = 30A$	$T_J = 125^{\circ}C$			0.7	
$I_R$	Reverse Maximum Leakage Current (per diode)*	$V_R = 45V$	$T_J = 25^{\circ}C$			2	mA
		$V_R = 45V$	$T_J = 125^{\circ}C$			75	
$C_d$	Junction Capacitance	$V_R = 5 V$	$f = 1 MHz$		900		pF

\*Pulse test  $t_p=300\mu s$   $\delta \leq 2\%$

Parameter			Unit
$R_{TH(j-c)}$	Maximum Thermal Resistance Junction To Case	(per package)	1.3 $^{\circ}C/W$
$R_{TH(j-c)}$	Maximum Thermal Resistance Junction To Case	(per diode)	2.4 $^{\circ}C/W$